## American University of Beirut

Department of Electrical and Computer Engineering
EECE 311 - Electronic Circuits (Sections 1 \& 2)
Spring 2008

## HOMEWORK 2

Due Wednesday March 12, 2008 at 1:00 PM

## 1. Common Source Amplifier

The common-source stage shown below must provide a voltage gain of 10 and has a power budget of 1 mW .


The technology parameters are: $k_{n}^{\prime}=300 \mu \mathrm{~A} / \mathrm{V}^{2}, V_{t n}=0.45 \mathrm{~V}, V_{A n}=5 \mathrm{~V}$, $k_{p}^{\prime}=100 \mu \mathrm{~A} / \mathrm{V}^{2}, V_{t p}=-0.5 \mathrm{~V}$, and $\left|V_{A p}\right|=4 \mathrm{~V}$.

Assume in the following that for the DC quantities: $I_{D} \simeq \frac{1}{2} k^{\prime}\left(\frac{W}{L}\right) V_{O V}^{2}$.
a) Find the value of $(W / L)_{1}$
b) Find the required value of $V_{\text {BIAS }}$ if $(W / L)_{2}$ is (20/0.18).

## 2. Common Gate Amplifier

Design the common-gate stage shown below for an input impedance of $50 \Omega$ and voltage gain of 5 . Assume a power budget of 2 mW . You should determine the aspect ratio $(W / L)$ for the MOSFET, the value of $R_{\mathrm{D}}$ and the value of the current source $I_{1}$. The technology parameters are: $k_{n}^{\prime}=300 \mu \mathrm{~A} / \mathrm{V}^{2}$ and $V_{t n}=0.45 \mathrm{~V}$. Neglect channel-length modulation.


## 3. Emitter Follower

Design the emitter-follower circuit shown below for a power budget of 3 mW and an output impedance of $50 \Omega$. Neglect base width modulation, and assume that $\beta \rightarrow \infty$. Determine that value of $I_{\text {REF }}$ and the value of the ratio $A_{\mathrm{EI}} / A_{\mathrm{E} \text {-REF }}$.


## 4. MOSFET Cascode

For the cascode circuit shown below, assume $(W / L)=10 \mu \mathrm{~m} / 0.18 \mu \mathrm{~m}$ for all MOSFETs, and that $V_{\text {BIAS }}=0.9 \mathrm{~V}$. Use PSpice to plot the input-output characteristics ( $v_{o}$ versus $v_{i}$ ). Note that the body terminals are connected to the supplies (ground for NMOS and $V_{D D}$ for PMOS.) Determine from the plot the point at which the small-signal gain is maximum, in absolute value.
Now suppose the biasing circuitry that produces the above DC value of $v_{\mathrm{I}}$ incurs an error of $+/-20 \mathrm{mV}$. Explain what happens to the voltage gain.


Use the SPICE models posted on Moodle.

## 5. Miller's Theorem

Use Miller's theorem to estimate the input and output poles of the circuit shown below.
Neglect base-width modulation and the internal BJT capacitors.


## 6. Active Inductor

The circuit shown below is called an active inductor. Neglecting all other capacitances, and channel-length modulation, compute the input impedance $Z_{\text {in }}$. Use Bode’s rules to plot the magnitude of $Z_{\text {in }}$ and explain how it exhibits inductive behavior.


## 7. Cascode Frequency Response

We wish to design the cascode circuit shown below for an input pole frequency of 5 GHz and an output pole frequency of 10 GHz . Assume $Q_{1}$ and $Q_{2}$ are identical, $I_{\mathrm{D}}=0.5 \mathrm{~mA}$, $C_{G S}=\frac{2}{3} W \times L \times C_{o x}, C_{o x}=12 \mathrm{fF} / \mu^{2}, \mu_{\mathrm{n}} C_{o x}=100 \mu \mathrm{~A} / \mathrm{V}^{2}, \lambda=0, L=0.18 \mu \mathrm{~m}$,
$C_{G D}=C_{0} \times W$, where $C_{0}=0.2 \mathrm{fF} / \mu \mathrm{m}$. Determine the maximum allowable values of $R_{\text {sig }}$ and $R_{\mathrm{D}}$, and the voltage gain. Use Miller's approximation for $C_{G D}$. Assume an overdrive voltage of 200 mV for each MOSFET.


